



SUU15N15-95
Vishay Siliconix

N-Channel 150-V (D-S) 175°C MOSFET

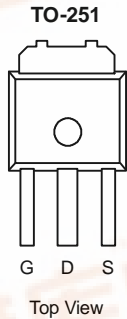
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
150	0.095 @ V _{GS} = 10 V	15
	0.100 @ V _{GS} = 6 V	15

FEATURES

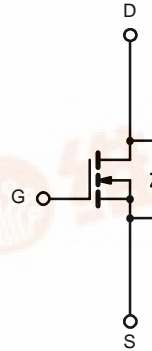
- TrenchFET® Power MOSFETS
- 175°C Junction Temperature
- 100% R_g Tested

APPLICATIONS

- Primary Side Switch



Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUU15N15-95

ABSOLUTE MAXIMUM RATINGS (T _C = 25°C UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	150	V	
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current (T _J = 175°C) ^b	I _D	T _C = 25°C	15	
		T _C = 125°C	8.7	
Pulsed Drain Current	I _{DM}	25	A	
Continuous Source Current (Diode Conduction)	I _S	15		
Avalanche Current	I _{AR}	15		
Repetitive Avalanche Energy (Duty Cycle ≤ 1%)	L = 0.1 mH	E _{AR}	11.3	mJ
Maximum Power Dissipation	P _D	T _C = 25°C	62 ^b	W
		T _A = 25°C	2.7 ^a	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 sec	16	20
		Steady State	45	55
Junction-to-Case (Drain)	R _{thJC}	2	2.4	°C/W

Notes:
^a Surface Mounted on 1" x 1" FR4 Board.
^b See SOA curve for voltage derating.



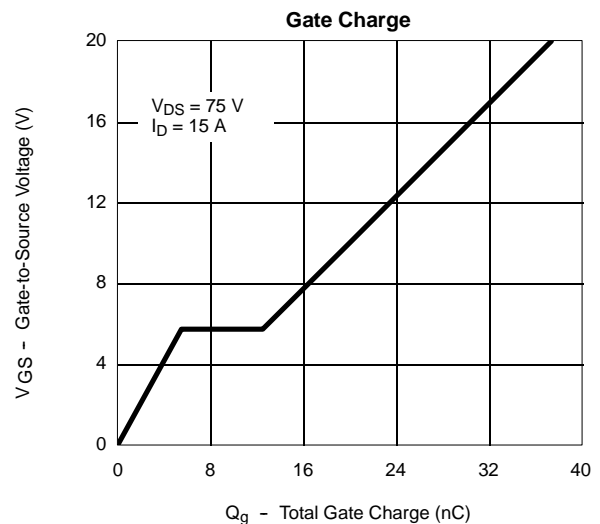
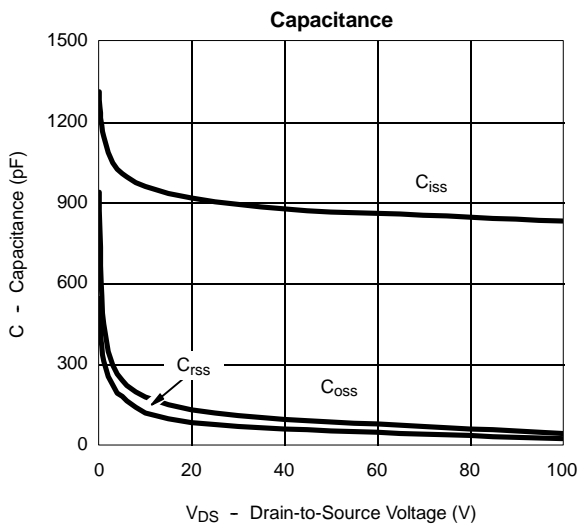
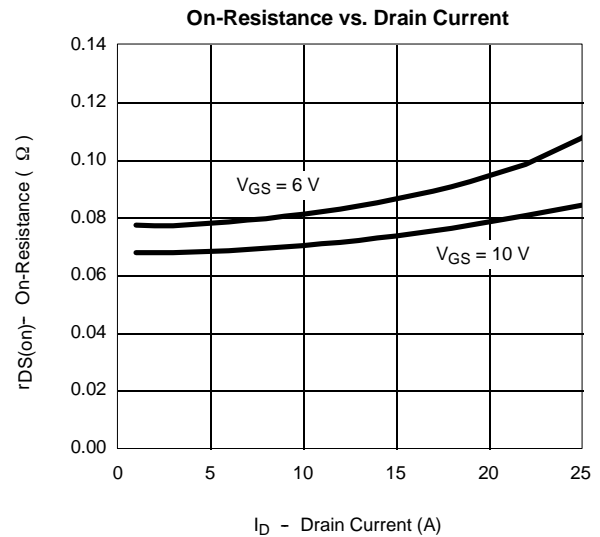
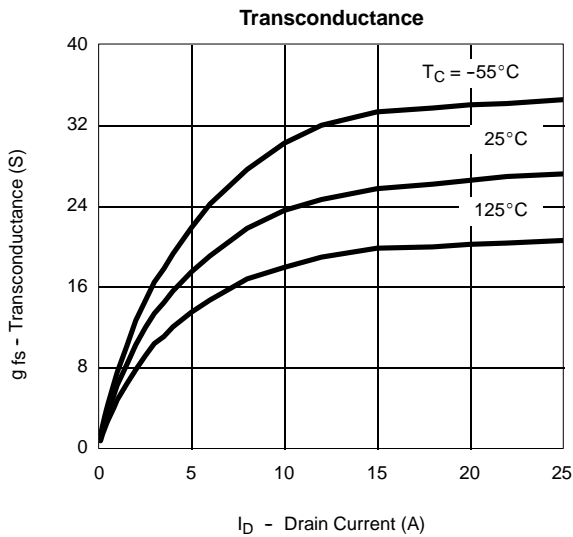
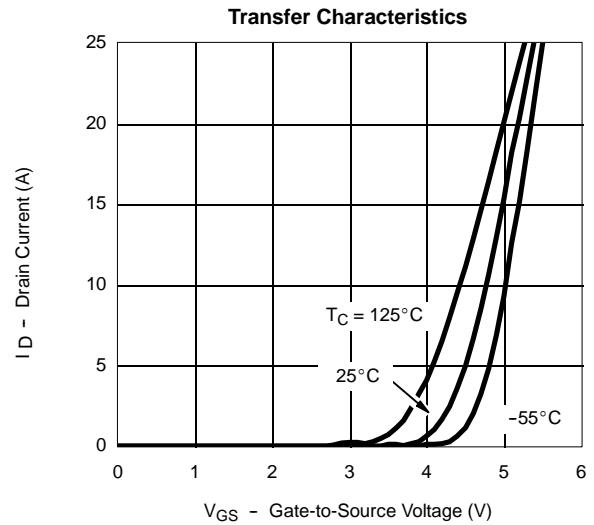
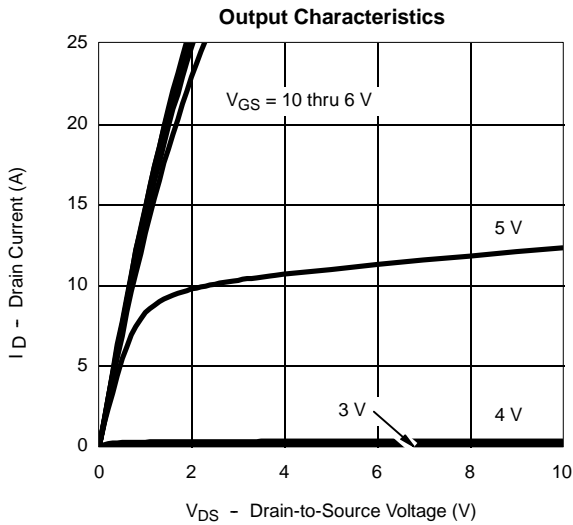
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	150			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V			1	μA
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	25			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.077	0.095	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.190	
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.250	
		V _{GS} = 6 V, I _D = 10 A		0.081	0.100	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		25		S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		900		pF
Output Capacitance	C _{oss}			115		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Q _g	V _{DS} = 75 V, V _{GS} = 10 V, I _D = 15 A		20	25	nC
Gate-Source Charge ^c	Q _{gs}			5.5		
Gate-Drain Charge ^c	Q _{gd}			7		
Gate Resistance	R _g		1		3.6	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 75 V, R _L = 5 Ω I _D ≅ 15 A, V _{GEN} = 10 V, R _g = 2.5 Ω		8	12	ns
Rise Time ^c	t _r			35	55	
Turn-Off Delay Time ^c	t _{d(off)}			17	25	
Fall Time ^c	t _f			30	45	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I _{SM}				25	A
Diode Forward Voltage ^b	V _{SD}	I _F = 15 A, V _{GS} = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		55	85	ns

Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- c. Independent of operating temperature.

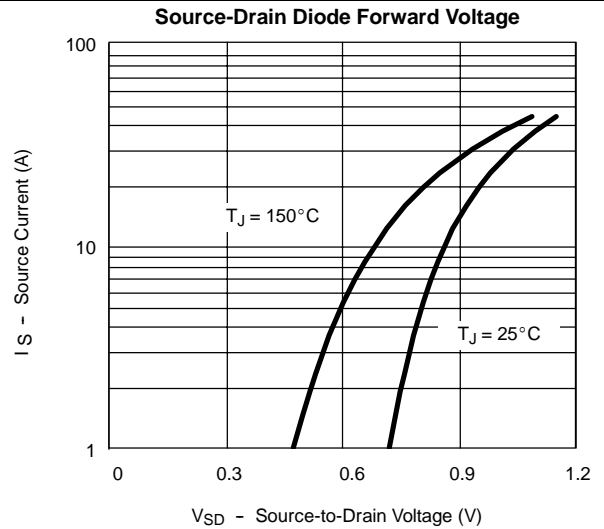
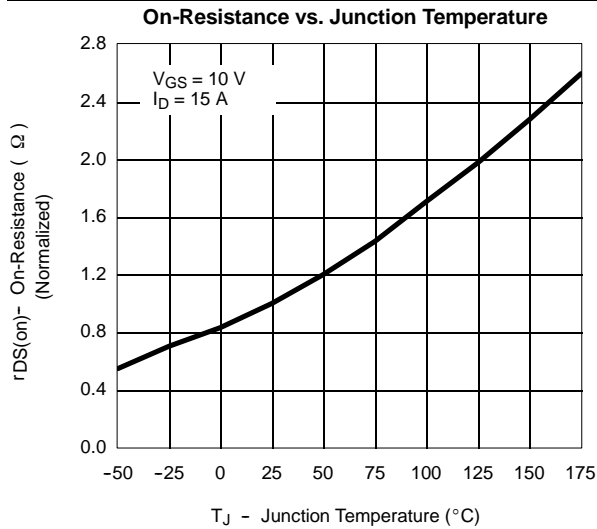


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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THERMAL RATINGS

